MIL-PRF-38534 CERTIFIED FACILITY

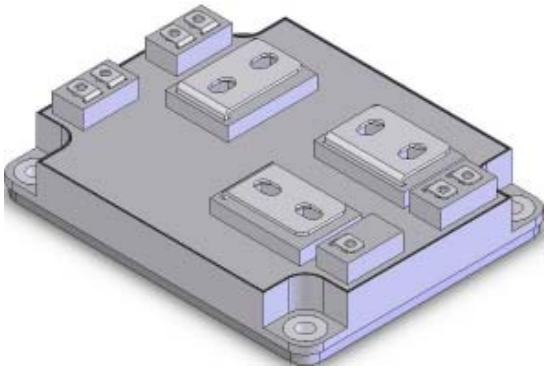
M.S.KENNEDY CORP.

600V/800A HALF BRIDGE PEM 4802

4707 Dey Road Liverpool, N.Y. 13088 (315) 701-6751

FEATURES:

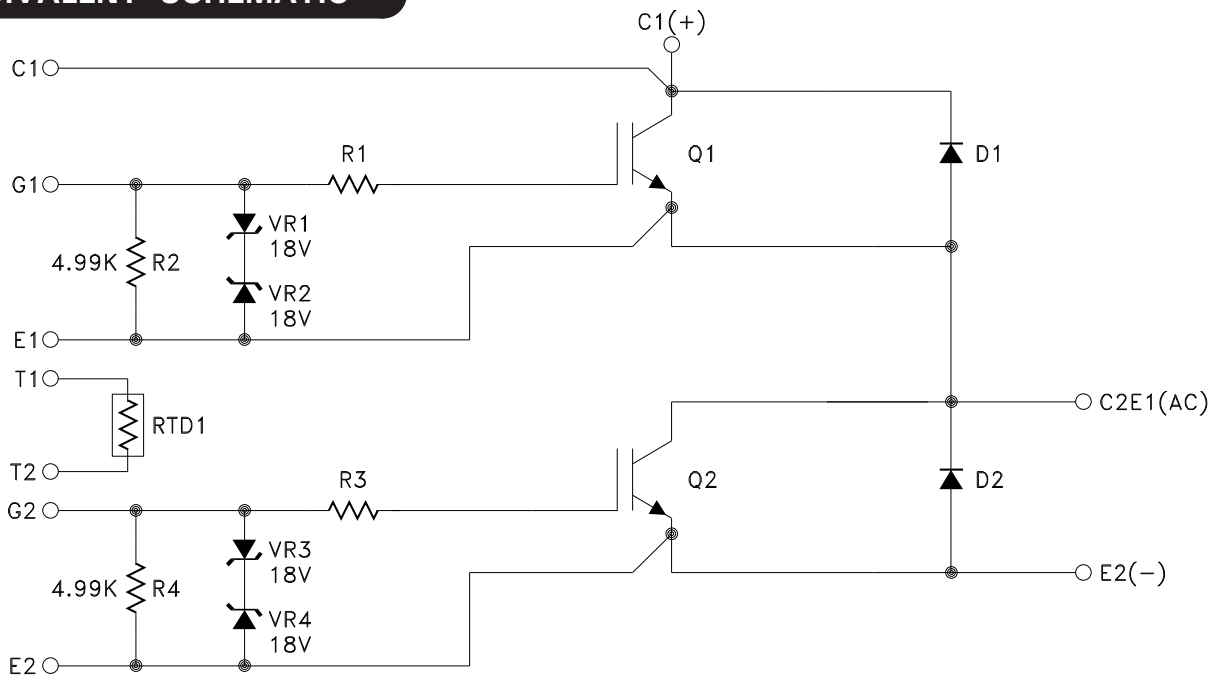
- Half Bridge Configuration
- 600V Rated Voltage
- 800A Continuous Output Current
- Internal Zener Clamps on Gates; Internal RTD
- Proprietary Encapsulation Provides Near Hermetic Performance
- HI-REL Screening Available (Modified 38534)
- Light Weight Domed ALSIC Baseplate
- Robust Mechanical Design for Hi-Rel Applications
- Ultra-Low Inductance Internal Layout
- Withstands 96 Hours HAST and Thermal Cycling (-55°C to +125°C)
- High Side Collector Sense Pin for De-Sat Detection



DESCRIPTION:

The MSK 4802 is one of a family of plastic encapsulated modules (PEM) developed specifically for use in military, aerospace and other severe environment applications. The half bridge configuration and 600 volt/800 amp rating make it ideal for use in high current motor drive and inverter applications. The Aluminum Silicon Carbide (AlSiC) baseplate offers superior flatness and light weight; far better than the copper or copper alloys found in most high power plastic modules. The high thermal conductivity materials used to construct the MSK 4802 allow high power outputs at elevated baseplate temperatures. Our proprietary coating, SEES™ - Severe Environment Encapsulation System - protects the internal circuitry of MSK PEM's from moisture and contamination, allowing them to pass the rugged environmental screening requirements of military and aerospace applications. MSK PEM's are also available with industry standard silicone gel coatings for a lower cost option.

EQUIVALENT SCHEMATIC



TYPICAL APPLICATIONS

- Motor Drives
- Inverters

ABSOLUTE MAXIMUM RATING ⑧

V_{CE}	Collector to Emitter Voltage 600V	T_{ST}	Storage Temperature Range . . -55°C to +125°C
V_{GE}	Gate to Emitter Voltage . . . . . ±20V	T_J	Junction Temperature . . . . . 150°C
I_{OUT}	Current (Continuous) 800A	T_C	Case Operating Temperature Range
I_{OUTP}	Current Pulsed (1mS) 1000A		MSK 4802H. . . . . -55°C to +125°C
V_{CASE}	Case Isolation Voltage . . . . . 2500 V		MSK 4802 . . . . . -40°C to +85°C

ELECTRICAL SPECIFICATIONS

Parameter ⑦	Test Conditions	Group A Subgroup	MSK 4802 H Min.	MSK 4802 H Typ.	MSK 4802 H Max.	MSK 4802 Min.	MSK 4802 Typ.	MSK 4802 Max.	Units
R(RTD) ②	V_{CE}=0V, V_{GE}=0V, I_C=0A	1	Nom -4	-	Nom +4	Nom -6	-	Nom +6	Ω
		2	Nom -7	-	Nom +7	-	-	-	Ω
Collector-Emitter Saturation Voltage	I_C=800A, V_{GE}=15V	1	-	2.3	2.6	-	2.3	2.8	V
		2	-	2.5	2.8	-	-	-	V
		3	-	3.2	3.8	-	-	-	V
Collector-Emitter Leakage Current	V_{CE}=600V, V_{GE}=0V	1	-	0.1	1	-	0.1	1	mA
		2	-	2.0	5	-	-	-	mA
Gate Threshold Voltage	I_C=100mA, V_{CE}=V_{GE}	1	3.5	4.1	7.5	3.3	4.1	7.8	V
		2	3.0	3.5	7.5	-	-	-	V
		3	4.0	4.5	8.5	-	-	-	V
Diode Forward Voltage	I_C=800A	1	-	1.6	2.5	-	1.6	2.7	V
		2	-	1.4	2.1	-	-	-	V
		3	-	1.8	2.5	-	-	-	V
Total Gate Charge ①	V=300V, I_C=800A	4	-	4.0	6.5	-	4.0	6.5	uC
E(on) ①	V=300V, I_C=800A, RG=5Ω, V_{GE}=-7/+15V	4	-	21	-	-	21	-	mJ
	V=300V, I_C=400A, RG=5Ω, V_{GE}=-7/+15V	4	-	11	20	-	11	20	mJ
	V=300V, I_C=800A, RG=5Ω, V_{GE}=-7/+15V	5	-	TBD	-	-	-	-	mJ
	V=300V, I_C=400A, RG=5Ω, V_{GE}=-7/+15V	5	-	TBD	-	-	-	-	mJ
E(off) ①	V=300V, I_C=800A, RG=10Ω, V_{GE}=-7/+15V	4	-	120	-	-	120	-	mJ
	V=300V, I_C=400A, RG=10Ω, V_{GE}=-7/+15V	4	-	60	90	-	60	90	mJ
	V=300V, I_C=800A, RG=10Ω, V_{GE}=-7/+15V	5	-	TBD	-	-	-	-	mJ
	V=300V, I_C=400A, RG=10Ω, V_{GE}=-7/+15V	5	-	TBD	-	-	-	-	mJ
Diode Reverse Recovery Time ①	I_E=800, di/dt=2500A/uS	4	-	120	-	-	120	-	nS
	I_E=400, di/dt=2500A/uS	4	-	110	-	-	110	-	nS
	I_E=800, di/dt=2500A/uS	5	-	TBD	-	-	-	-	nS
	I_E=400, di/dt=2500A/uS	5	-	TBD	-	-	-	-	nS
Diode Reverse Recovery Energery①	I_E=800, di/dt=2500A/uS	4	-	1.5	-	-	1.5	-	mJ
	I_E=400, di/dt=2500A/uS	4	-	1.0	5	-	1.0	5	mJ
	I_E=800, di/dt=2500A/uS	5	-	TBD	-	-	-	-	mJ
	I_E=400, di/dt=2500A/uS	5	-	TBD	-	-	-	-	mJ
Thermal Resistance ①	IGBT @ T_J=125°C	-	-	0.030	0.042	-	0.030	0.042	°C/W
	DIODE @ T_J=125°C	-	-	0.032	0.045	-	0.032	0.045	°C/W

NOTES:

① Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
② R(RTD) nominal is case temperature dependent. R(RTD) nominal equals 1000Ω +(3.85* T_{CASE} °C).
③ Industrial grade devices shall be tested to subgroup 1 unless otherwise specified.
④ HI-REL grade devices ("H" suffix) shall be 100% tested to subgroups 1, 2 and sample tested to subgroup 3.
⑤ Subgroup 4 testing available upon request.
⑥ Subgroup 1, 4 T_A = +25°C
2, 5 T_A = +125°C
3, T_A = -55°C
⑥ Unless otherwise specified all specifications apply to both the upper and lower sections of the half bridge.
⑦ V_{GE}=15V unless otherwise specified.
⑧ Continuous operation at or above absolute maximum ratings may adversly effect the device performance and/or life cycle

THERMAL CALCULATIONS

Power dissipation and maximum allowable temperature rise involve many variables working together. Collector current, PWM duty cycle and switching frequency all factor into power dissipation. DC losses or "ON-TIME" losses are simply V_{CE}(SAT) x Collector Current x PWM duty cycle. For the MSK 4802, V_{CE}(SAT) = 2.6V max., and at 800 amps and a PWM duty cycle of 30%, DC losses equal 624 watts. Switching losses vary proportionally with switching frequency. The MSK 4802 typical switching losses at V_{CE} = 300V and I_{CE} = 800A are about 141mJ, which is simply the sum of the turn-on switching loss and the turn-off switching loss. Multiplying the switching frequency times the switching losses will result in a power dissipation number for switching. The MSK 4802, at 5KHz, will exhibit switching power dissipation of 705 watts. The total losses are the sum of DC losses plus switching losses, or in this case, 1329 watts total.

1329 watts x 0.042°C/W thermal resistance equals 55.8 degrees of temperature rise between the case and the junction. Subtracting 55.8°C from the maximum junction temperature of 150°C equals 94.2°C maximum case temperature for this example.

V_{CE}(SAT) x IC x PWM duty cycle = 2.6V x 800 amps x 30% = 624 watts DC losses

Turn-on switching loss + Turn-off switching loss = Total switching losses = 21 + 120 = 141mJ

Total switching loss x PWM frequency = Total switching power dissipation = 141mJ x 5KHz = 705 watts

Total power dissipation = DC losses + switching losses = 624 + 705 = 1329 watts

Junction temperature rise above case = Total power dissipation x thermal resistance

1329 watts x 0.042°C/W = 55.8°C temperature rise above case

Maximum junction temperature - junction temperature rise = maximum baseplate temperature

150°C - 55.8°C = 94.2°C

TYPICAL PERFORMANCE CURVES

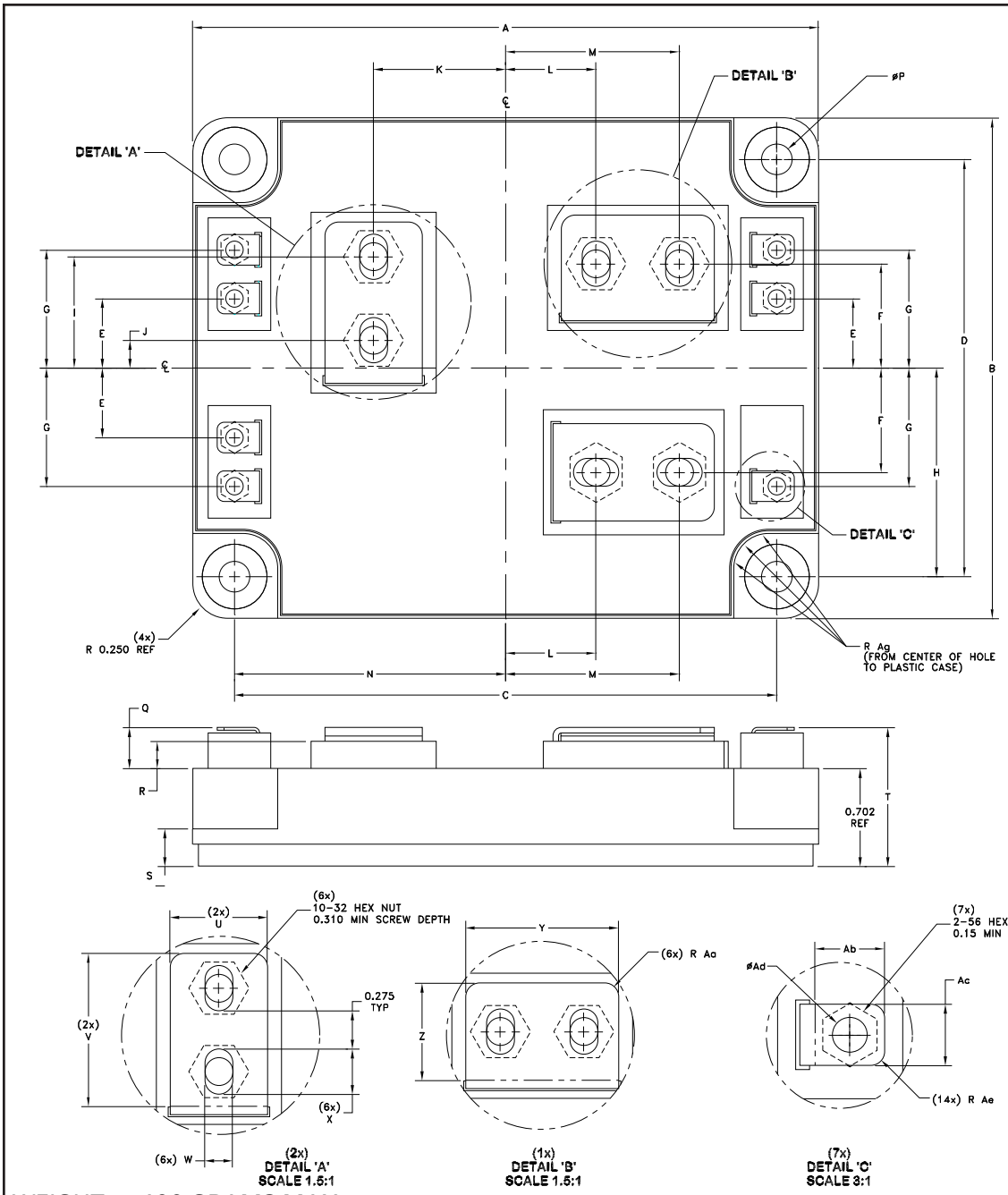
TBD

SCREENING CHART

OPERATION	INDUSTRIAL	H SUFFIX
QUALIFICATION (MODIFIED)	NO	YES
ELEMENT EVALUATION	NO	YES
CLEAN ROOM PROCESSING	YES	YES
NON DESTRUCT BOND PULL SAMPLE	YES	YES
CERTIFIED OPERATORS	NO	YES
MIL LINE PROCESSING	YES	YES
MAX REWORK SPECIFIED	NO	YES
ENCAPSULANT	GEL COAT	SEES™
PRE-CAP VISUAL	YES - INDUSTRIAL	YES - CLASS H
TEMP CYCLE (-55°C TO +125°C)	NO	YES
BURN-IN	NO	YES - 160 HOURS
ELECTRICAL TESTING	YES - 25°C	YES - FULL TEMP
EXTERNAL VISUAL	YES - SAMPLE	YES
XRAY	NO	NO
PIN FINISH	NI	NI

NOTE: ADDITIONAL SCREENING IS AVAILABLE SUCH AS XRAY, CSAM, MECHANICAL SHOCK, ETC. CONTACT FACTORY FOR QUAL STATUS.

MECHANICAL SPECIFICATIONS



REF	MIN	MAX
A	4.470	4.530
B	3.580	3.610
C	3.890	3.910
D	2.990	3.010
E	0.450	0.550
F	0.745	0.755
G*	0.800	0.900
H	1.495	1.505
I	0.795	0.805
J	0.195	0.205
K*	0.945	0.955
L*	0.645	0.655
M*	1.245	1.255
N	1.945	1.955
P	0.208	0.225
Q	0.240	———
R	0.130	———
S	0.262	0.272
T	0.990	1.010
U	0.700	0.750
V	1.050	1.150
W	0.195	0.230
X	0.310	0.340
Y	1.085	1.115
Z	0.700	0.750
Aa*	0.100	———
Ab	0.250	0.280
Ac	———	0.270
Ad	0.120	0.130
Ae*	0.050	———
Af	0.000	0.008
Ag*	———	0.250

WEIGHT = 400 GRAMS MAX.

ORDERING INFORMATION

MSK4802 H

SCREENING

BLANK = INDUSTRIAL; H = HI-REL (MODIFIED 38534)

GENERAL PART NUMBER

THE ABOVE EXAMPLE IS A MILITARY SCREENED MODULE.

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